Icemos Technology Ltd Product Specification 1000.564001 Issue Date 17 December 2019 11

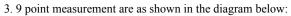
Part Number Customer

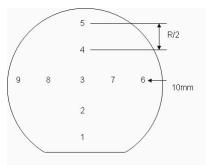
Category	Parameter		Specification	Measurement Method
OverallWafer	1.0	Diameter	150.00 +/- 0.30 mm	
	2.0	Primary Flat Orientation	{110}+/- 0.5 degree	Wafer Vendor
	3.0	Primary Flat Length	57.50 +/- 2.50 mm	Wafer Vendor
	4.0	Overall Thickness	434.00 +/- 7.00 μm	ADE, 100%
	5.0	LPDs > 0.3um	<30	Tencor Particle counter
	6.0	Frontsurface condition	Polished, roughness <5A	Guaranteed by process
	7.0	Total Thickness Variation (TTV)	<6.00μm	Guaranteed by Process
	8.0	Bow	<60.00μm	ADE to ASTM F534, 100%
	9.0	Warp	<60.00μm	
	10.0	Edge Chips	0	Bright Light, 100%
	11.0	Edge Exclusion	5mm	
	12.0	Lasermarking	On wafer BACKSIDE	Guaranteed by process
HandleSilicon	13.0	Handle Growth Method	CZ	Wafer Vendor
	14.0	Handle Orientation	{100} +/- 0.5 degree	Wafer Vendor
	15.0	Handle Thickness	400.00 +/- 6.00 μm	ADE, 100%
	16.0	Handle Doping Type	N	Wafer Vendor
	17.0		Phosphorous	Wafer Vendor
	18.0	-	3 ∼ 5 Ohmcm	Wafer Vendor
	19.0	Backside Finish	Polished with lasermark and oxide	Wafer Vendor
BuriedOxide	20.0	Oxide Type	Thermal	
	21.0	Oxide Thickness	40,000.00 +/- 2,000.00 A	Nanospec centre point, 4%
	22.0	Oxide formed on	Handle and/or Device	•
DeviceSilicon	23.0	Device Growth Method	CZ	Wafer Vendor
	24.0	Device Orientation	{100} +/- 0.5 degree	Wafer Vendor
	25.0		30.00 +/- 0.50 μm	Filmetrics, 100% 9-Pt (note3)
	26.0	Distance to device silicon edge from wafer edge	<= 2mm	Typical by Process
	27.0	Device Doping Type	N	Wafer Vendor
	28.0	Device Dopant	Phosphorous	Wafer Vendor
	29.0	Device Resistivity	<=0.005 ohm-cm	Wafer Vendor
	30.0	•	none	IR Inspection, 100%
	31.0		0	Bright Light, 100% (note 2)
	32.0		none	Bright Light, 100% (note 2)
	33.0		Polished, roughness < 2.5 A.	Guaranteed by process

Page 1 of 2 15/11/2021 www.icemostech.com

teemos reemioiozv	Eta	Todact Specification	1000:501001	155de Bate 17 Beechioef 2019 11
Part Number		Customer		
Category	Parameter	Specification		Measurement Method
Shipping Details	Wafer per box :	Max 25		
	Packaging:	Taped Polypropylene Wafer Box Empak, Ultrapak, 150.00mm Antistatic Double Bagging	:	
	Lot Shipment Data	Device Thickness Bow / Warp Data Handle and SOI Thickness		
Explanatory Notes	1. Microscope inspec	tion performed using microscope sca	ın as below. 5x objecti	ive.
	2. All bright light ins	pections performed exclude all wafer	area outside the edge	exclusion defined in Overall

2. All bright light inspections performed exclude all wafer area outside the edge exclusion defined in Overal Wafer, Edge Exclusion. High intensity bright lamp inspection as per ASTM F523.





Additional Information